DISCRETE SEMICONDUCTORS

DATA SHEET

PDTA143T series PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

Product data sheet Supersedes data of 2003 Sep 08 2004 Aug 04



PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PDTA143T series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
R1	bias resistor	4.7	_	kΩ
R2	open	_	_	_

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TVDE NUMBER	PAC	(AGE	MARKING CORE	NDN COMPLEMENT
TYPE NUMBER	PHILIPS	EIAJ	MARKING CODE	NPN COMPLEMENT
PDTA143TE	SOT416	SC-75	39	PDTC143TE
PDTA143TEF	SOT490	SC-89	10	PDTC143TEF
PDTA143TK	SOT346	SC-59	45	PDTC143TK
PDTA143TM	SOT883	SC-101	E6	PDTC143TM
PDTA143TS	SOT54 (TO-92)	SC-43	TA143T	PDTC143TS
PDTA143TT	SOT23	ı	*42 ⁽¹⁾	PDTC143TT
PDTA143TU	SOT323	SC-70	*45 ⁽¹⁾	PDTC143TU

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTA143TS	1 R1 R1 3 MAM362	1 2 3	base collector emitter
PDTA143TE PDTA143TEF PDTA143TK PDTA143TT PDTA143TU	3 1 R1 3 1 DDB272	1 2 3	base emitter collector
PDTA143TM	2 R1 3 1 Bottom view MDB268	1 2 3	base emitter collector

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PDTA143T series

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	_	-50	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
Io	output current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT23	note 1	_	250	mW
	SOT54	note 1	_	500	mW
	SOT323	note 1	_	200	mW
	SOT346	note 1	_	250	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air		
	SOT23	note 1	500	K/W
	SOT54	note 1	250	K/W
	SOT323	note 1	625	K/W
	SOT346	note 1	500	K/W
	SOT416	note 1	833	K/W
	SOT490	note 1	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

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PDTA143T series

CHARACTERISTICS

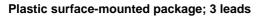
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ mA}$	200	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	_	_	-150	mV
R1	input resistor		3.3	4.7	6.1	kΩ
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	3	pF

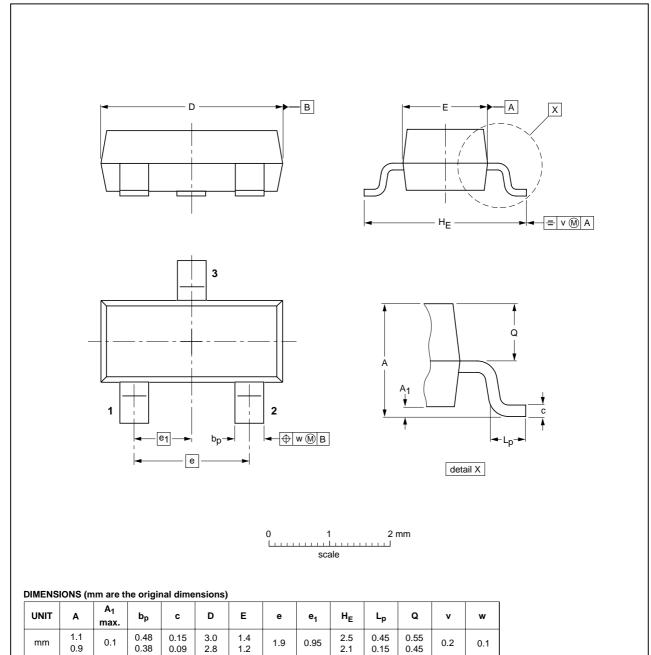
PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PDTA143T series

PACKAGE OUTLINES



SOT23



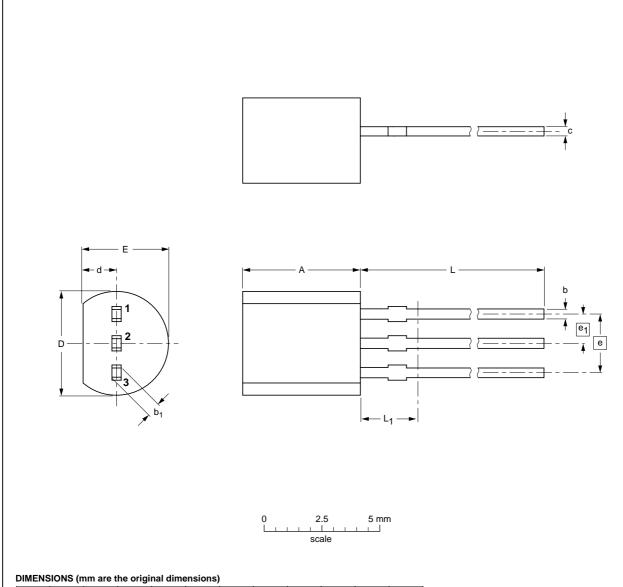
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION		
SOT23		TO-236AB			04-11-04 06-03-16	
SO123		TO-236AB			06-03	

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PDTA143T series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

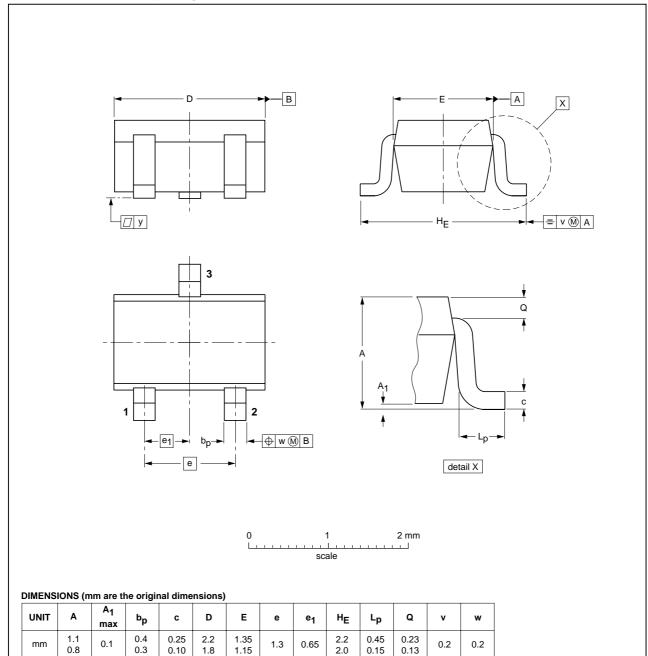
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A		-04-06-28 04-11-16	

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PDTA143T series

Plastic surface-mounted package; 3 leads

SOT323



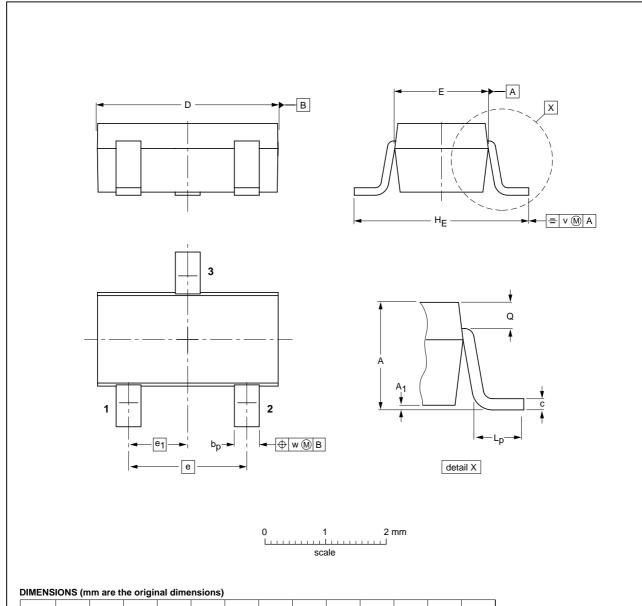
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT323			SC-70		04-11-04 06-03-16	

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PDTA143T series

Plastic surface-mounted package; 3 leads

SOT346



UNIT	Α	A ₁	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

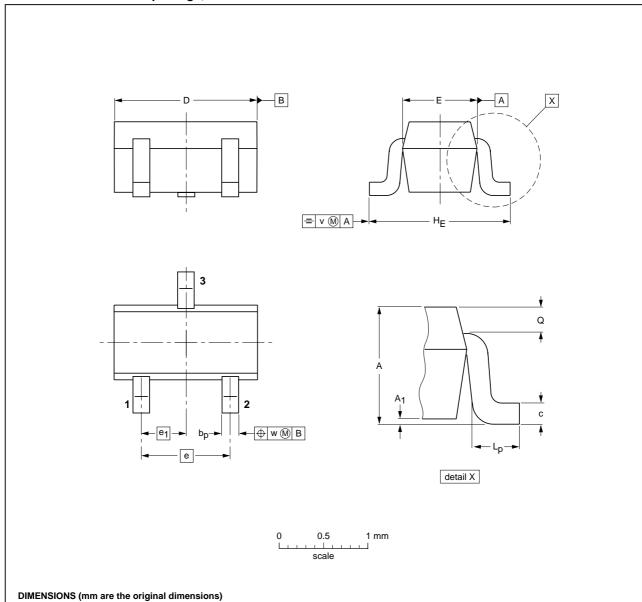
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59A		04-11-11 06-03-16	

PNP resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$, R2 = open

PDTA143T series

Plastic surface-mounted package; 3 leads

SOT416



UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	ø	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION		
SOT416			SC-75		04-11-04 06-03-16	

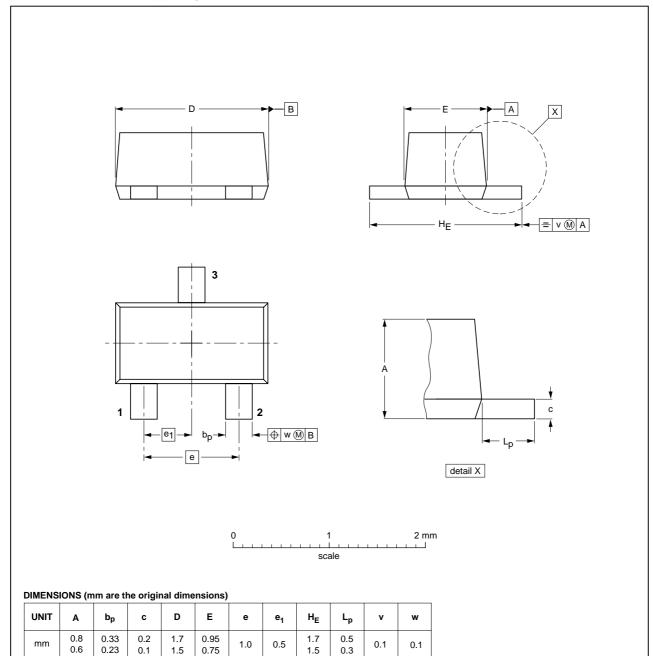
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PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PDTA143T series

Plastic surface-mounted package; 3 leads

SOT490



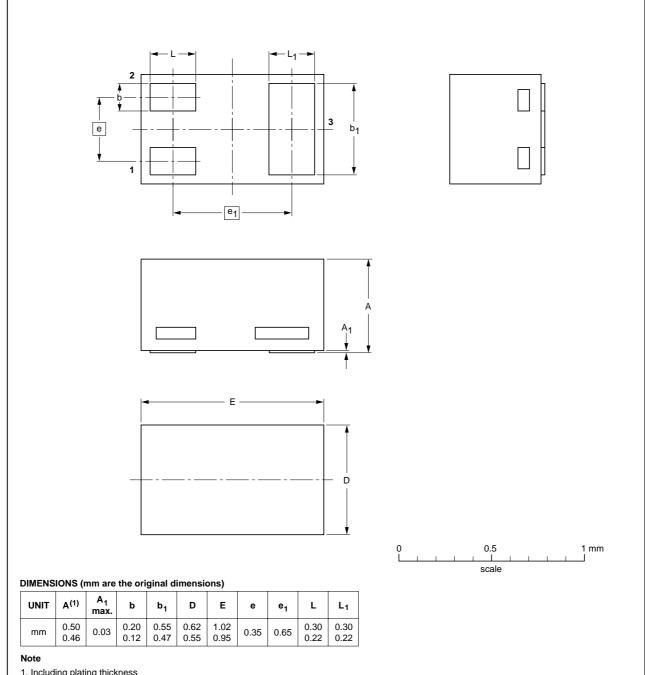
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT490			SC-89	$ \ \ \bigoplus \big($	05-07-28 06-03-16

PNP resistor-equipped transistors; $R1 = 4.7 \text{ k}\Omega$, R2 = open

PDTA143T series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



1. Including plating thickness

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT883			SC-101		03-02-05 03-04-03	

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PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PDTA143T series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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Contact information

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